

### Product Summary

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	$I_D$
-30V	60mΩ@-10V	-5.1A
	70mΩ@-6V	
	105mΩ@-4.5V	

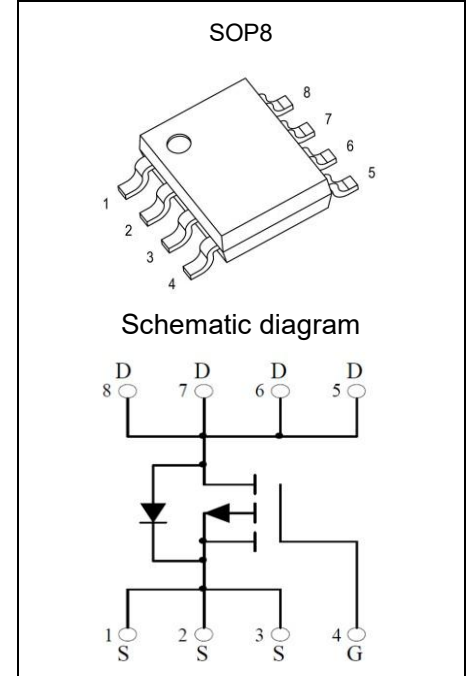
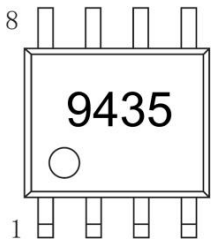
### Feature

- TrenchFET Power MOSFET
- Excellent  $R_{DS(on)}$  and Low Gate Charge

### Application

- Load Switch for Portable Devices
- Battery Switch

### MARKING:



### ABSOLUTE MAXIMUM RATINGS ( $T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	-30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current	$I_D$	-5.1	A
Plused Drain Current	$I_{DM}$	-20	A
Single Pulsed Avalanche Energy*	$E_{AS}$	20	mJ
Power Dissipation	$P_D$	1.4	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	89	$^\circ\text{C}/\text{W}$
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature	$T_{STG}$	-55~ +150	$^\circ\text{C}$

\* EAS condition:  $V_{DD}=-50\text{V}$ ,  $L=0.5\text{mH}$ ,  $R_G=25\Omega$ , Starting  $T_J = 25^\circ\text{C}$

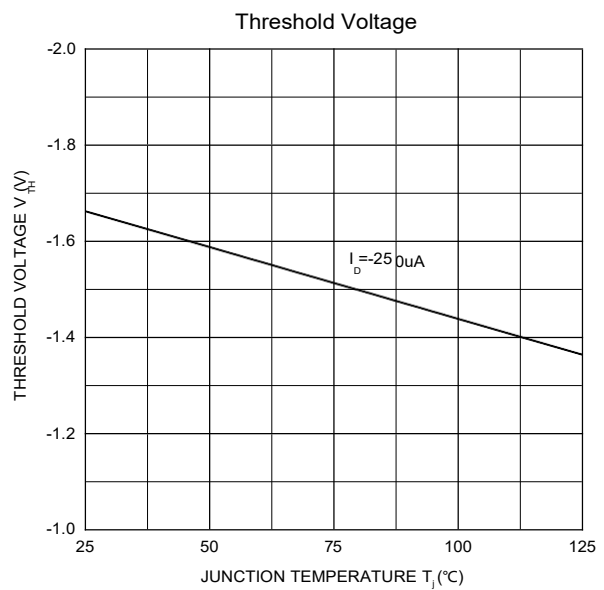
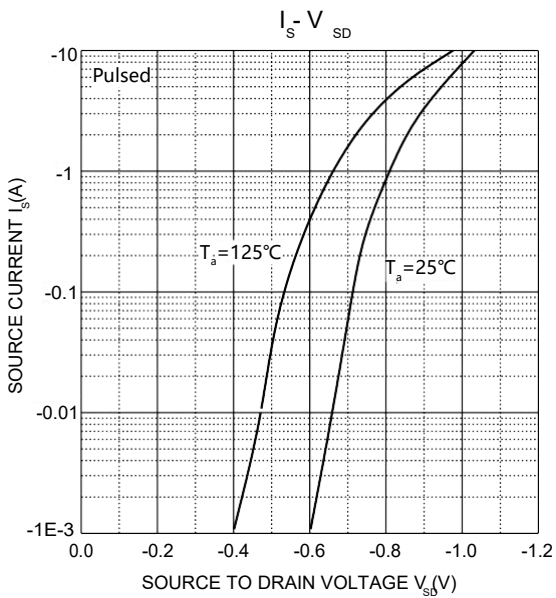
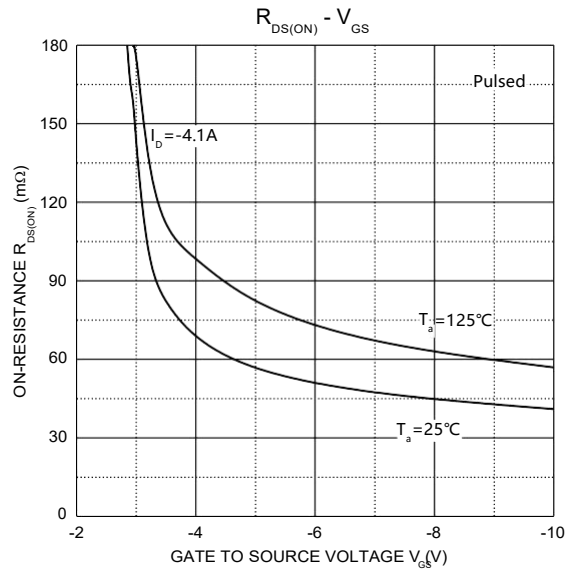
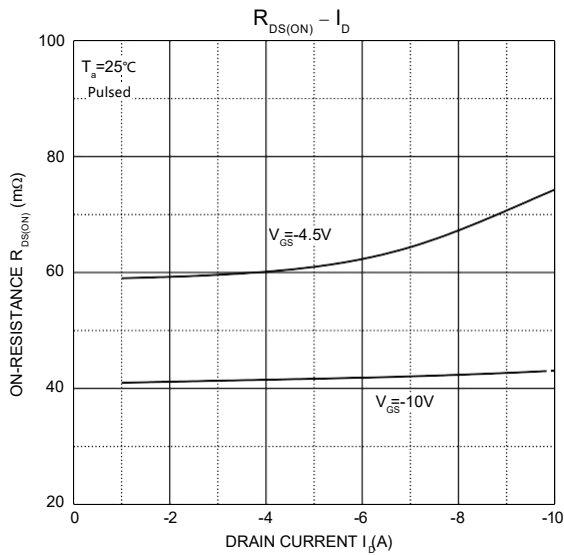
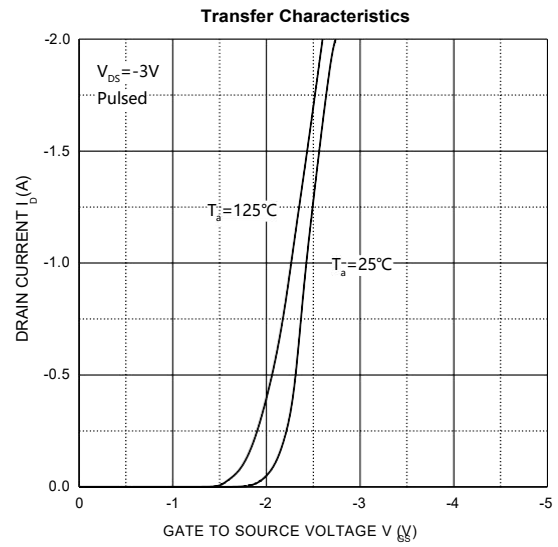
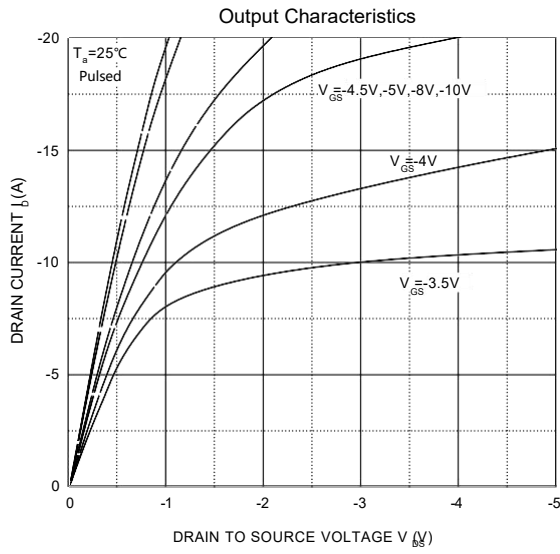
**MOSFET ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise noted)**

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
<b>Off characteristics</b>						
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA	-30.5			V
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = -24V, V <sub>GS</sub> = 0V			-1	μA
Gate-body leakage current	I <sub>GSS</sub>	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V			±100	nA
<b>On characteristics<sup>(1)</sup></b>						
Gate threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	-1.0	-1.5	-2.0	V
Drain-source on-resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = -10V, I <sub>D</sub> = -4.6A			60	mΩ
		V <sub>GS</sub> = -6V, I <sub>D</sub> = -4.1A			70	
		V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -2A			105	
Forward transconductance	g <sub>FS</sub>	V <sub>DS</sub> = -15V, I <sub>D</sub> = -4.6A	5			S
<b>Switching characteristics<sup>(2)</sup></b>						
Total gate charge	Q <sub>g</sub>	V <sub>DS</sub> = -15V, V <sub>GS</sub> = -10V, I <sub>D</sub> = -4.6A			40	nC
Gate-source charge	Q <sub>gs</sub>			4		
Gate-drain charge	Q <sub>gd</sub>			6.3		
Turn-on delay time	t <sub>d(on)</sub>	V <sub>DD</sub> = -15V, I <sub>D</sub> = -1A, V <sub>GS</sub> = -10V, R <sub>G</sub> = 6Ω, R <sub>L</sub> = 15Ω			30	ns
Turn-on rise time	t <sub>r</sub>				60	
Turn-off delay time	t <sub>d(off)</sub>				120	
Turn-off fall time	t <sub>f</sub>				100	
<b>Drain-Source Diode characteristics</b>						
Diode Forward voltage <sup>(1)</sup>	V <sub>SD</sub>	V <sub>GS</sub> = 0V, I <sub>S</sub> = -2.6A			-1.2	V
Continuous drain-source diode forward current	I <sub>S</sub>				-5.1	A
Pulsed drain-source diode forward current	I <sub>SM</sub>				-20	A

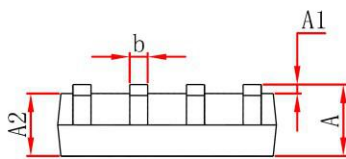
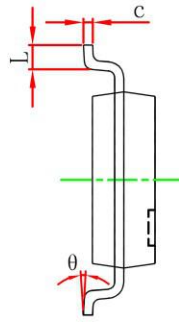
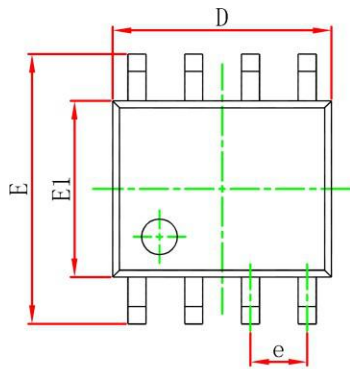
Notes:

1. Pulse Test : Pulse Width ≤ 300μs, duty cycle ≤ 2%.
2. Guaranteed by design, not subject to production testing.

## Typical Electrical and Thermal Characteristics



SOP-8 Package Information

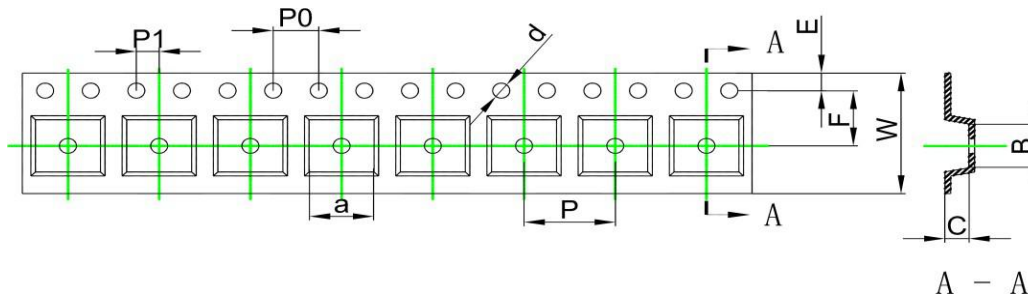


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.007	0.010
D	4.800	5.000	0.189	0.197
e	1.270 (BSC)		0.050 (BSC)	
E	5.800	6.200	0.228	0.244
E1	3.800	4.000	0.150	0.157
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°



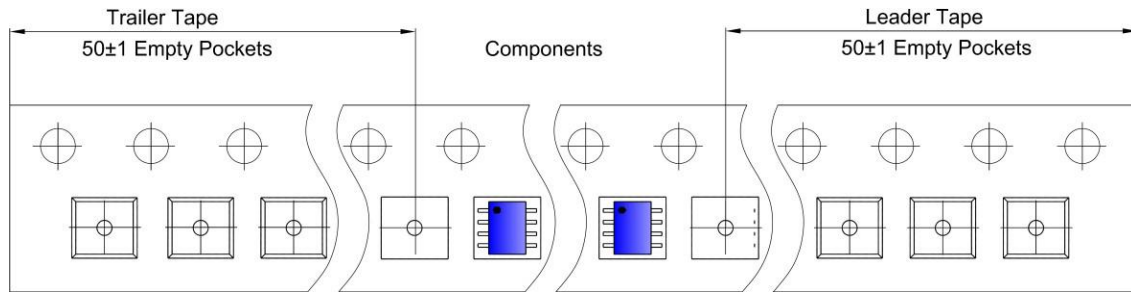
SOP8 Tape and Reel

SOP8 Embossed Carrier Tape

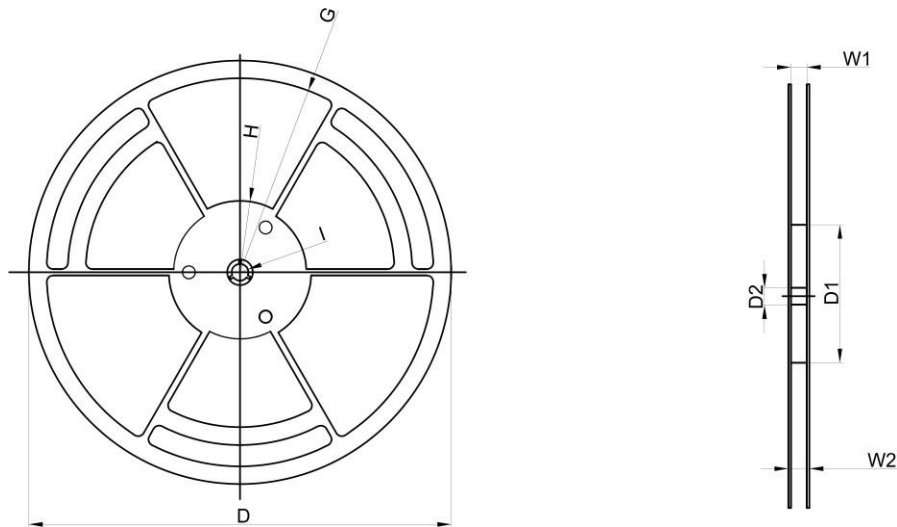


Dimensions are in millimeter										
Pkg type	a	B	C	d	E	F	P0	P	P1	W
SOP8	6.40	5.40	2.10	Φ1.50	1.75	5.50	4.00	8.00	2.00	12.00

SOP8 Tape Leader and Trailer



SOP8 Reel



Dimensions are in millimeter								
Reel Option	D	D1	D2	G	H	I	W1	W2
13`Dia	Φ330.00	100.00	13.00	R151.00	R56.00	R6.50	12.40	17.60

Reel	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
2,500pcs	13 inch	2,500pcs	336×336×48	20,000pcs	445×355×365	